Letter

Resonant Inelastic X -Ray Scattering (R IX S) in SrC uO 2

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The resonant inelastic x-ray scattering (RIXS) was measured in an insulating SrCuO₂ with changing the incident photon energy (h) near the Cu 1s absorption edge (K-edge). Complex structures and their dependences on the momentum transfer(k) and h were observed. The h dependence of the RIXS spectra measured for a constant k=2.4 has shown a remarkable enhancement near the absorption maximum and a shift of the spectral weight toward larger loss-energy with increasing h. Also, the energy of the inelastic loss peak in the RIXS spectra for the xed excitation at 8.993 keV, 10 eV below the absorption maximum, has shown a clear dependence on k. These results are in a qualitative agreement with a theoretical prediction. Full utilization of the potential of the high brilliance X ray light source at BL19LXU of SP ring-8 with 27 m long insertion device will open up a breakthrough in RIXS for heavy transition metal compounds in accordance with the improvement in focussing and analyzing elements.

KEYW ORDS: resonant inelastic X-ray scattering, RIXS, one dimensional antiferrom agnetic insulator

Electronic structures of many transition metal compounds with strong electron correlation have intensively been studied from both theoretical as well as experimental points of view.^{1,2)} Angle-resolved photoemission spectroscopy (ARPES) has been very useful for probing occupied electronic states of metallic as well as semiconducting materials. For example a lot of high resolution studies have been performed for high T_c cuprate superconductors.³⁾ However, ARPES requires ultrahigh vacuum condition and very clean and specular single crystal sample surfaces. Still high resolution ARPES at low photon energy (h) is rather surface sensitive and sometimes the obtained results are not consistent with the bulk electronic structures.^{4,5)} Inverse angle resolved photoemission studies are also surface

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sensitive and their energy resolutions are not high enough to study unoccupied electronic states in detail. Moreover both techniques are not applicable to insulators. Bulk intrinsic information on unoccupied electronic states together with the occupied states is required in order to fully understand the electronic structures of such materials as high T_C cuprates and colossal magnetoresistance manganites.⁶⁽⁸⁾ For example, studies of the wave number (k) dependence of the Mott-Hubbard gap will provide useful information on the electron correlation electron.

In order to satisfy both bulk sensitivity and k resolution, the inelastic X-ray scattering has recently been developed.⁹⁽¹¹⁾ In general, the inelastic X-ray scattering from the valence charge distribution is very weak and thus di cult to be distinguished with good statistics from the total scattering signal. Therefore resonance enhancement by the excitation near the core excitation threshold is often utilized.

We have performed the resonance inelastic X-ray scattering (RIXS) for single crystalline SrCuO₂, which is a typical one dimensional (ID) antiferrom agnetic insulator. A theoretical study of RIXS for 1D copper oxides has predicted h and k dependences of the RIXS spectra $.^{12)}$ The SrCuO₂ has two Cu-O chains (c-axis) combined to each other by edge-sharing and is reported to show the spin-charge separation behavior with 1D nature.¹³⁾ In general, these insulating copper oxides have the lower H ubbard band (LHB) in the occupied part and the upper H ubbard band (UHB) in the unoccupied part separated by a M ott-H ubbard gap. R IXS experiment can probe the excitation across this M ott-H ubbard gap. O ne of the advantages of R IXS is the freedom to choose h near the core absorption threshold, resulting in di erent interm ediate states. In this Letter, we report the spectral changes as functions of the h and m omentum transfer k, demonstrating the resonance enhancem ent behavior near the Cu 1s edge (K-edge).

The experiment was carried out in the third hutch of the beam line BL19LXU¹⁴⁾ at SP ring-8. The linearly polarized light is delivered from an in-vacuum 27 m long insertion device. The experimental setup for RIXS is schematically shown in Fig. 1. The undulator radiation tuned to a proper h is monochromatized by two Si (111) crystals. It is further monochromatized by two channel-cut Si (220) crystals. The full width at half maximum (FW HM) of the energy resolution of the excitation photons is thus set to 0.3 eV. Then the monochromatic light is incident onto the polished surface of SrCuO₂ kept at room temperature in an evacuated chamber with polyim id windows. The horizontally scattered radiation by the sample with the momentum (or wave number k) transfer (k) parallel to the Cu-O chain is analyzed by a spherically bent Si (553) crystal. The diameter of the Roland circle is set to 1 m. The radiation from the analyzer is focused on the detector. The total energy resolution, determ ined from the quasi-elastic scattering from the sample, has a width of about 0.6 eV (FW HM). Our RIXS measurem ent has been perform ed in two modes: O ne

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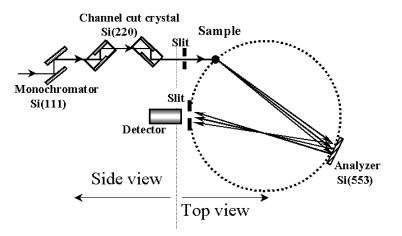


Fig. 1. Schem atic illustration of the experim ental setup for R IX S m easurem ents For sim plicity, a side view and a top view are shown for the front and the rear parts, respectively.

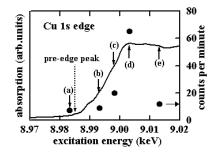


Fig. 2. Absorption spectrum of $SrCuO_2$. The solid arrows and labels (a) (e) indicate the excitation energies at which R IX S spectra were measured.

for dierenth near the Culsedge (K-edge) (h 9.005 keV) with xing k to 2.4 and the other for dierent k with xing h at 8.993 keV.

The solid curve in Fig.2 displays the absorption spectrum of SrCuO₂ near the Cu K-edge, obtained by means of the uorescence yield. The solid arrows in Fig.2 indicate the h at which the RIXS spectra are measured. The pre-edge peak indicated by the dashed arrow corresponds to the Cu 1s-3d quadrupole transition.¹⁵⁾ In the monovalent copper compounds, the Cu 3d orbital is fully occupied and such an excitation is forbidden. Therefore, the observation of this pre-edge structure is consistent with the divalent character of Cu in this compound, though its intensity is not so strong. We then observe structures near 8.99 and 8.997 keV. These structures are ascribable to dipole allowed transitions from the Cu 1s to Cu 4p states.¹⁵⁾ The structure near the label (d) is ascribed to the Cu 1s-Cu 4p transition. Figure 3 shows the inelastic scattering spectrum in a wide loss energy region for h = 8.993 keV (label (b) in Fig.2) at k = 2.2. This measurement is performed just to know the

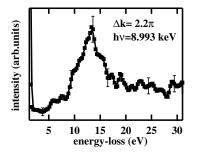


Fig. 3. The wide energy-boss spectra observed at h = 8.993 keV. The momentum transfer k is 2.2.

wide energy behavior, so that no patience is paid to get a good S/N ratio. The characteristic peak near 14 eV is identified as the resonant R am an scattering related to the excitation from the Cu 3d to 4p states or to the Cu K $_5$ em ission line.¹⁶⁾

The k dependence of the R IX S spectra was measured at h = 8.993 keV as sum marized in Fig. 4. The raw data spectral shapes clearly show the k dependence. However, the S/N ration is not su cient to determ ine the peak energies. This is because the employed h is much below the absorption peak energy and therefore the resonance enhancement is not so strong (see Fig. 2). Therefore, we employed the least square t by assuming G aussian peaks with the FW HM = 0.6eV, which could simulate the elastic peak. The t results are shown in Fig.4 (b). Still multiple peaks are observed for each k. The spectrum at k=2.2has a structure overlapping with the tail of the elastic peak. So the energy of this peak is determined from the second energy derivative. The energy positions of the peak indicated

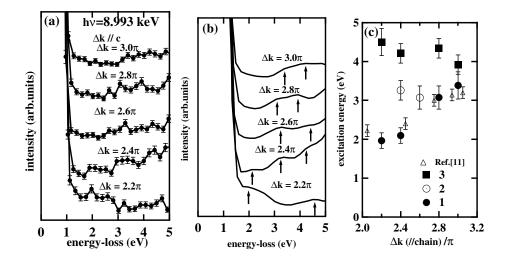


Fig. 4. (a)D ependence of the RIXS spectra on the momentum transfer k along the chain direction for a xed h = 8.993 keV. The (b) is the r results. (c)P lot of the peak positions against k. The results by H assan et al.¹¹⁾ are included for comparison.

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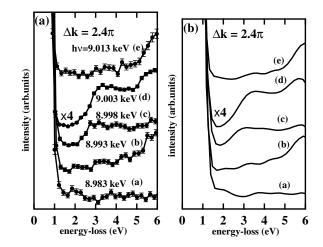


Fig. 5. h dependence of the RIXS spectra of $SrCuO_2$ for a xed momentum transfer of 2.4. The spectrum (d) is shown after the reduction of a factor 4.

by the arrows are plotted in Fig.4 (c) together with the result of ref.11. The error bars were determined by FW HM of each peak. There seem to be three dispersions represented by the marks 1, 2 and 3. The peak 1 shifts toward larger loss energy with the increase of k. The peak 2 separated from the peak 1 for k=2.4 m erges with the peak 1 for k=2.6 and 2.8. The peak 3 does not shift much with k. These whole results are in qualitative agreem ent with Fig.1 of ref.11. Though the statistics of our present results are slightly worse than those in ref.11, the minimum energy in our experiment is slightly lower than that of the previous results.

Then the h dependence of RIXS was measured for xed k = 2.4 as summarized in Fig. 5. The raw data spectral shapes clearly show the h dependence. We again employed the least square t by assuming G aussian peaks. The tresults are shown in Fig.5 (b). In Figs. 5 (a) and (b), the spectrum (d) is shown after the reduction of a factor 4. This means that the inelastic peak intensity is greatly enhanced at the excitation very near the absorption m axim um . On the other hand, the spectrum (a) shows a small structure at even larger loss energy than the result at h = 8.993 keV and k = 2.2. The spectrum (b) has three structures in the region within 5 eV and has a large structure near 6 eV. The spectra (c) and (d) have a large structure in the region between 2.5 and 4.5 eV. The excitation energy for (e) is far away from that of (d) and the loss peak within 5 eV becomes very weak again compared with the results for the excitations (c) and (d). The spectrum obtained under the excitations (a), (b), (c), and (e) show only 5 or 6 counts per channel and per m inute for the loss region within 5 eV. On the other hand, the count of the spectrum obtained under the excitation (d) has more than 60 counts perm inute (right scale in Fig.2.). The h dependence of the intensity distribution of the RIXS spectra is already predicted in ref.11. The present

experimental results for k = 2.4 (0.4 o set from 2) with the shift of the spectral weight toward larger loss energy with increasing h is consistent with this theoretical prediction. Besides, the structure near 6 eV may be ascribed to a charge transfer excitation from the ground state to the antibonding-type excited state.¹¹⁾ It is already mentioned that the spectral shape within 5 eV changes much with h . The loss energy peak near 2 eV is observed for (a) and (b), whereas it becomes less obvious for the excitations (c), (d), and (e). In the case of (a), the excitation has a strong character of the quadrupole Cu 1s-Cu 3d excitation and the observed structure near 2 eV can be assigned to the excitation from LHB to UHB. The loss peak near 2 eV in (b) may reject either the contribution of the quadrupole Cu 1s-Cu 3d excitation or the interatom ic hybridization between the Cu 3d and the Cu 4p orbitals.For h in (c) and (d), the contribution of the quadrupole excitation. Then the structure near 2 eV is much suppressed due to the di erent symmetry of the intermediate state. The M ott gap excitation below 2eV is consistent with the bulk sensitive ARPES with the strong peak near 0.95eV at /2 corresponding to the LHB.¹⁷⁾

In order to do a full-dress study of R IX S processes in $SrCuO_2$, we plan to do k resolved m easurements at several dierent h with much higher energy resolution by improving the analyzer crystals and fully utilizing the high intensity of the powerful 27 m long insertion light source.

In this Letter, we have reported on R IX S in insulating SrC uO₂. It is found that R IX S spectra change m uch with h re ecting the character of the intermediate states. The k resolved R IX S results are consistent with the bulk sensitive soft X -ray ARPES as well as a theoretical prediction based on an extended Hubbard m odel.

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